

Features

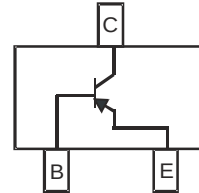
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complimentary NPN Type Available (DNLS320A)
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**



SOT-23

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-5	A
Repetitive Peak Pulse Current (Note 3)	I_{CRP}	-3	A
Continuous Collector Current	I_C	-2	A
Base Current	I_B	-0.5	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ $T_A = 25^\circ\text{C}$	P_D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 3) @ $T_A = 25^\circ\text{C}$	$R_{\theta JA}$	209	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Operated under pulsed conditions: pulse width $\leq 100\text{ms}$, duty cycle ≤ 0.25 .
 4. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 5)						
Collector-Base Cutoff Current	I _{CB0}	—	—	-100	nA	V _{CB} = -20V, I _E = 0
		—	—	-50	μA	V _{CB} = -20V, I _E = 0, T _A = 150°C
Emitter-Base Cutoff Current	I _{EBO}	—	—	-100	nA	V _{EB} = -5V, I _C = 0
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-20	—	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-20	—	—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	—	—	V	I _E = -100μA
ON CHARACTERISTICS (Note 5)						
DC Current Gain	h _{FE}	220	—	—	—	V _{CE} = -2V, I _C = -0.1A
		220	—	—		V _{CE} = -2V, I _C = -0.5A
		200	—	—		V _{CE} = -2V, I _C = -1A
		150	—	—		V _{CE} = -2V, I _C = -2A
		100	—	—		V _{CE} = -2V, I _C = -3A
		—	—	—		I _C = -0.5A, I _B = -50mA
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	—	-80	mV	I _C = -1A, I _B = -50mA
		—	—	-150		I _C = -2A, I _B = -100mA
		—	—	-250		I _C = -2A, I _B = -200mA
		—	—	-230		I _C = -2A, I _B = -300mA
		—	—	-330		I _C = -3A, I _B = -300mA
		—	—	—		I _E = -2A, I _B = -200mA
Equivalent On-Resistance	R _{CE(SAT)}	—	90	115	mΩ	I _C = -2A, I _B = -100mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	—	-1.1	V	I _C = -3A, I _B = -300mA
Base-Emitter Turn-on Voltage	V _{BE(ON)}	—	—	-1.2	V	V _{CE} = -2V, I _C = -1A
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	100	215	—	MHz	V _{CE} = -5V, I _C = -100mA, f = 100MHz
Output Capacitance	C _{ob}	—	—	50	pF	V _{CB} = -10V, f = 1MHz

Notes: 5. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

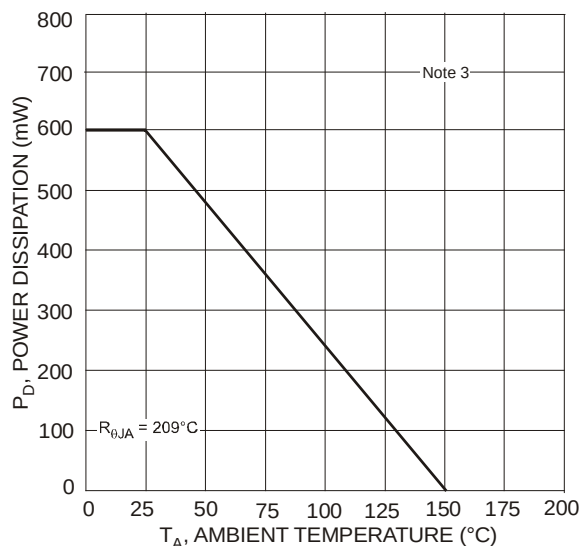


Fig. 1, Max Power Dissipation vs. Ambient Temperature

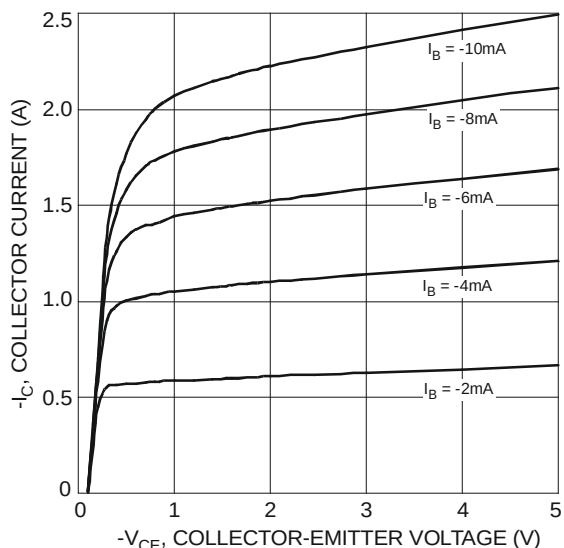


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

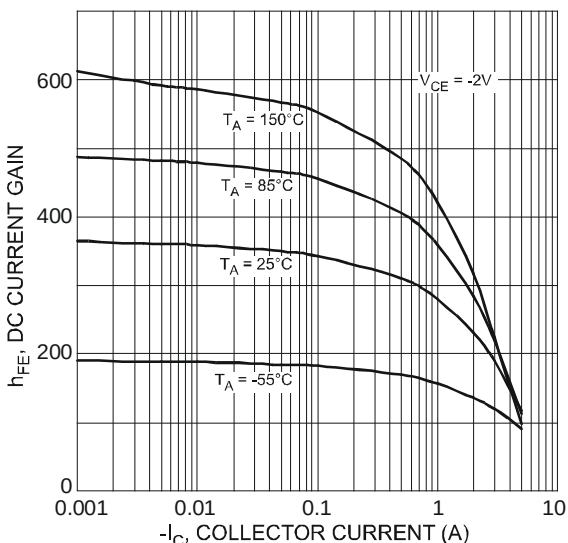


Fig. 3 Typical DC Current Gain vs. Collector Current

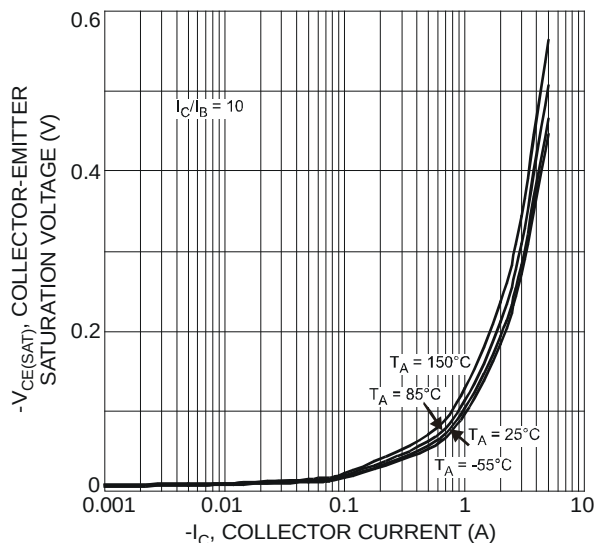


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

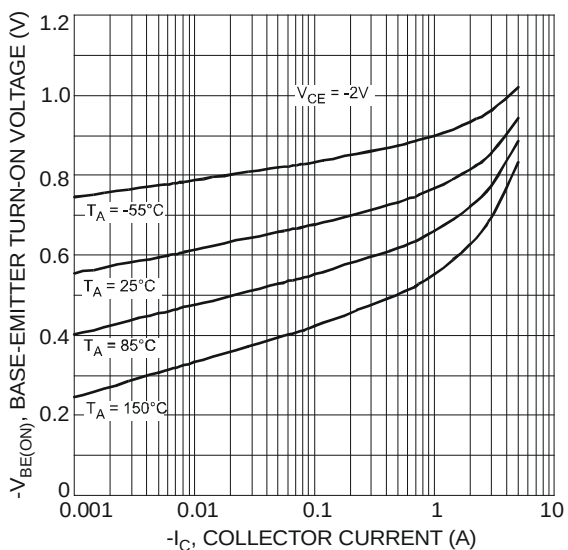


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

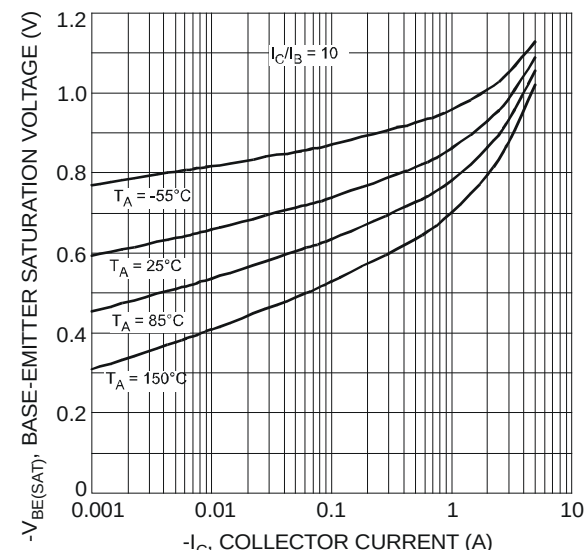


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

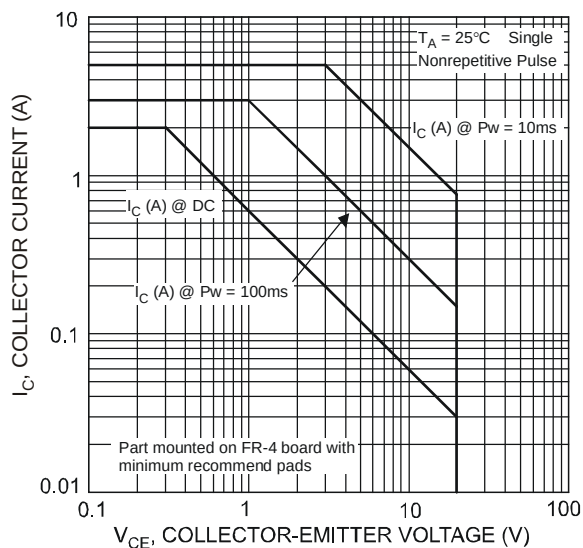


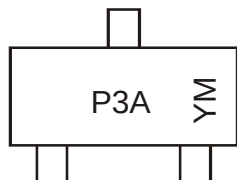
Fig. 7 Safe Operation Area

Ordering Information (Note 6)

Device	Packaging	Shipping
DPLS320A-7	SOT-23	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



P3A = Product Type Marking Code

YM = Date Code Marking

Y = Year (ex: V = 2008)

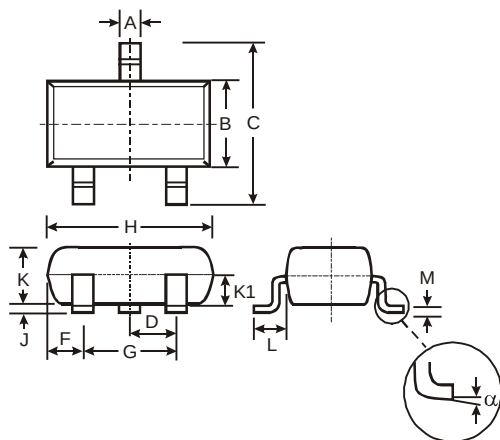
M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

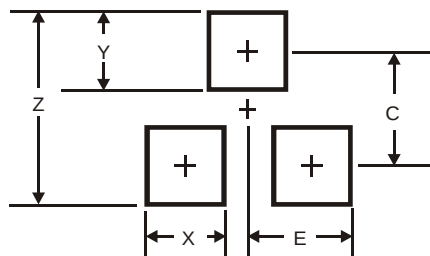
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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